Hits	Search Text	DB	Time stamp
56	semiconductor adj substrate and inductor and capacitor and radio adj frequency and	USPAT; US-PGPUB;	2002/05/17 17:36
		DERWENT; IBM_TDB	2002/05/17
130	(438/8).CCLS.	US-PGPUB; EPO; JPO; DERWENT;	16:26
114	(438/13).CCLS.	USPĀT; US-PGPUB; EPO; JPO;	2002/05/17 16:28
259	radio adj frequency adj detection or radio adj frequency adj detector	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/17 16:30
17251	chemical adj etching	DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/05/17 17:48
1	(radio adj frequency adj detection or radio adj frequency adj detector) and	DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/05/17 16:33
141	(chemical adj etching)	EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/05/17
15708	resonate	EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/05/17
13700	Tesonate	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	16:36
110	(chemical adj etching) and resonate	US-PGPUB; EPO; JPO; DERWENT;	2002/05/17
1133640	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 16:36
41	((chemical adj etching) and resonate) and semiconductor	USPAT; US-PGPUB; EPO; JPO;	2002/05/17 16:40
130	quartz adj crystal adj monitor	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/17 16:45
165128	receiver and transmitter	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/17
185	(chemical adj etching) and (receiver and transmitter)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 16:46
	56  130  114  259  17251  1  141  15708  110  1133640  41  130  165128	semiconductor adj substrate and inductor and capacitor and radio adj frequency and etching and monitoring  130 (438/8).CCLS.  114 (438/13).CCLS.  259 radio adj frequency adj detection or radio adj frequency adj detector  17251 chemical adj etching  1 (radio adj frequency adj detection or radio adj frequency adj detector) and (chemical adj etching)  141 lateral adj undercut  15708 resonate  110 (chemical adj etching) and resonate  1133640 semiconductor  41 ((chemical adj etching) and resonate) and semiconductor  130 quartz adj crystal adj monitor  165128 receiver and transmitter	Semiconductor adj substrate and inductor and capacitor and radio adj frequency and etching and monitoring  (438/8).CCLS.  (590, JPO;

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_			IISDAT I	2002/05/17
-	2	5629244.URPN.	USPAT	17:06
-	22	5639423.URPN.	USPAT	2002/05/17 17:10
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_	1	"5427946"   "5486335"   "5498392").PN. 5282921.URPN.	USPAT	2002/05/17 17:16
-	5	("2912497"   "2967907"   "3806643"   "4423137"   "4509162").PN.	USPAT	2002/05/17 17:17
-	256	(438/381).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 17:24
-	48	rf adj etch	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 17:41
-	5	5817573.URPN.	USPAT	2002/05/17 17:38
-	5	5817573.URPN.	USPAT	2002/05/17 17:38
-	14	("5141897"   "5167760"   "5231051"   "5233223"   "5254498"   "5312773"   "5326427"   "5358621"   "5364817"   "5374849"   "5387550"   "5397742"	USPAT	2002/05/17
-	1	"5407861"   "5496773").PN. "non-contact detection system" and (etch or etching)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 17:43
-	435	high adj frequency adj detection or high adj frequency adj detector	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 17:44
-	330600	etch or etching	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 17:45
   <b>-</b> 	653629	silicon	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 17:45
_	6	(high adj frequency adj detection or high adj frequency adj detector) and (etch or etching) and silicon	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 17:45
-	0	chemical adj etching and (high adj frequency adj detection or high adj frequency adj detector)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	
		"secondary ion emission spectroscopy"	IBM_TDB USPAT;	2002/05/19

	8	"leybold-inficon"	USPAT;	2002/05/19
-	l °	Teypoid inition.	US-PGPUB;	11:04
			EPO; JPO;	
			DERWENT;	
			IBM_TDB USPAT;	2002/05/19
-	405	radio adj waves and etching	US-PGPUB;	11:05
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			DERWENT;	
			IBM_TDB	
_	1133640	semiconductor	USPAT;	2002/05/19
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			EPO; JPO; DERWENT;	
			IBM TDB	
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	İ		USPAT;	2002/05/19
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_	5	("5140164"   "5629244"   "5733820"	USPAT	2002/05/19
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		"5856871"   "5891352"   "6210981").PN.		
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- 1	1	"thickness detection" same radio	USPAT;	2002/05/19
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			EPO; JPO;	
			DERWENT;	
į			IBM_TDB USPAT;	2002/05/19
-	4	"thickness detection" same rf	USPAL; US-PGPUB;	11:58
			EPO; JPO;	11.30
			DERWENT;	
			IBM TDB	
		"insitu" and etching and (rf or radio)	USPAT;	2002/05/19
-	14	and (monitoring or detection)	US-PGPUB;	12:03
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			DERWENT;	
			IBM TDB	
	6	("4115184"   "4207137"   "4354154"	USPĀT	2002/05/19
-	. "	"4963819"   "5175472"   "5273610").PN.		12:08
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_	144	"lateral undercut" or "lateral under-cut"	USPAT;	2002/05/19
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			DERWENT;	
			IBM_TDB	2002/05/19
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			IBM TDB	
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Ì		undered /	EPO; JPO;	
			DERWENT;	
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	1		DERWENT;	
	1		IBM_TDB	
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-	43622	undercut	US-PGPUB;	13:33
			EPO; JPO;	
1			DERWENT;	
	1		IBM_TDB	
1_	1134671	measured	USPAT;	2002/05/19
-	11340/1	meabaroa	US-PGPUB;	12:47
	1		EPO; JPO;	
			DERWENT;	
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			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	2002/05/19
-	653629	silicon	USPAT;	12:47
			US-PGPUB; EPO; JPO;	14.31
			DERWENT;	
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	ł		IBM TDB	1

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-	1209	(undercut and measured ) and silicon	USPAT;	2002/05/19
		`	US-PGPUB;	12:47
1			EPO; JPO;	
			DERWENT; IBM TDB	
			USPAT;	2002/05/19
-	596606	lateral	US-PGPUB;	12:48
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			DERWENT;	
			IBM_TDB	
<b>!</b> _	422	((undercut and measured ) and silicon )	USPAT;	2002/05/19
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	1		DERWENT;	
			IBM_TDB USPAT;	2002/05/19
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			EPO; JPO;	
			DERWENT;	i l
			IBM TDB	
	1	(((undercut and measured ) and silicon )	USPĀT;	2002/05/19
-	-	and lateral) and insitu	US-PGPUB;	13:32
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			DERWENT;	
			IBM_TDB	2002/05/19
-	3	("4763183"   "5114233"   "5539766").PN.	USPAT	13:03
		FROODS AND	USPAT	2002/05/19
-	5	5739909.URPN.	ODIAI	13:04
	0.50	(224/228) CCIS	USPAT;	2002/05/19
-	252	(324/329).CCLS.	US-PGPUB;	13:32
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1_	57	(324/341).CCLS.	USPAT;	2002/05/19
ı		·	US-PGPUB;	13:32
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-	264	(324/338).CCLS.	US-PGPUB;	13:32
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		((324/341).CCLS.) or ((324/338).CCLS.) or	EPO; JPO;	13.31
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-	43622	undercut	US-PGPUB;	15:22
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			DERWENT;	
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_	0	(sra or "surface resistance analyzer")	USPAT;	2002/05/20
		and undercut and semiconductor	US-PGPUB;	15:23
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	i		DERWENT; IBM TDB	
	1	" C	USPAT;	2002/05/20
-	276	(sra or "surface resistance analyzer")	US-PGPUB;	15:23
	1	and semiconductor	EPO; JPO;	10.20
	1		DERWENT;	
	1		IBM TDB	
	120620	etch	USPAT;	2002/05/20
-	128630	E C C II	US-PGPUB;	15:23
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			DERWENT;	
			IBM_TDB	
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			IBM_TDB	2002/05/20
_	256	(438/381).CCLS.	USPAT; US-PGPUB;	17:08
			EPO; JPO;	17.00
			DERWENT;	
			IBM TDB	
	70005	du du aban	USPAT;	2002/05/20
-	70905	inductor	US-PGPUB;	17:09
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			DERWENT;	
			IBM_TDB	
_	76	((438/381).CCLS.) and inductor	USPAT;	2002/05/21
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			EPO; JPO;	
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-	17	((438/381).CCLS.) and inductor and	USPAT; US-PGPUB;	09:32
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	1		DERWENT;	
			IBM TDB	
1 .	1	(257/49) CCIS	USPAT;	2003/06/02
- '	961	(257/48).CCLS.	US-PGPUB;	08:01
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	817207	coil	USPĀT;	2003/06/02
-	1 01/20/		US-PGPUB;	08:01
]			EPO; JPO;	
		1	DERWENT;	
i .			IBM_TDB	2002/06/02
		((257/48).CCLS.) and coil	USPAT;	2003/06/02
_	15	((20)) 10) 100	1 TEC. 07 DITE *	08:03
-	15	((237) 137 132 237)	US-PGPUB;	1
-	15	((2017,10),000,000	EPO; JPO;	
-	15	((257, 15), 0502257, 2515	EPO; JPO; DERWENT;	
-			EPO; JPO; DERWENT; IBM_TDB	2003/06/02
-	1481		EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/06/02
-			EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/06/02 08:03
-			EPO; JPO; DERWENT; IBM_TDB USPAT;	

				2222/25/22
	128	coil and (lateral adj etch or lateral adj	USPAT;	2003/06/02 08:07
		etching)	US-PGPUB; EPO; JPO;	08:07
	ļ l		DERWENT;	
	!		IBM TDB	
	0000004	measure or measured or measuring	USPAT;	2003/06/02
-	2082394	measure or measured or measuring	US-PGPUB;	08:08
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			DERWENT;	
			IBM_TDB	2002/06/02
_	81	(coil and (lateral adj etch or lateral	USPAT;	2003/06/02 08:08
		adj etching)) and (measure or measured or	US-PGPUB; EPO; JPO;	08:08
	1	measuring)	DERWENT;	
			IBM TDB	
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_	4	( 5/59909 / .EN.	US-PGPUB;	08:24
	1		EPO; JPO;	
			DERWENT;	i
			IBM_TDB	2003/06/03
<b>-</b>	11	5739909.URPN.	USPAT	2003/06/02 08:22
		1 HE CONTROL OF THE C	USPAT	2003/06/02
-	3	("4763183"   "5114233"   "5539766").PN.	ODENI	08:23
	100	ttowamatry	USPAT;	2003/06/02
-	182	scatterometry	US-PGPUB;	08:24
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000 (00 (00
_	18	coil and scatterometry	USPAT;	2003/06/02
			US-PGPUB; EPO; JPO;	06:37
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			IBM TDB	
	0.44700	monitor or monitoring	USPAT;	2003/06/02
-	844792	monitor of monitoring	US-PGPUB;	08:38
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			DERWENT;	
			IBM_TDB	2003/06/02
-	23	coil and (lateral adj etch or lateral adj	USPAT; US-PGPUB;	08:44
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-	//609	Inductor	US-PGPUB;	08:45
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l			DERWENT;	
1			IBM_TDB	2003/06/02
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1			IBM_TDB	
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-	1096		US-PGPUB;	08:46
1			EPO; JPO;	
ł			DERWENT;	
		a la la la la la la la chahinal	<pre>IBM_TDB USPAT;</pre>	2003/06/02
-	1		US-PGPUB;	08:47
		and ((438/14).CCLS.)	EPO; JPO;	
	1		DERWENT;	
	l .		IBM TDB	
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